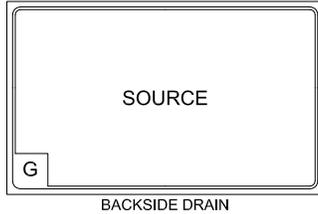


CP406-CWDM3011N

N-Channel MOSFET Die

Enhancement-Mode

The CP406-CWDM3011N is a silicon N-Channel MOSFET designed for high speed pulsed amplifier and driver applications.



MECHANICAL SPECIFICATIONS:

Die Size	63.8 x 38.9 MILS
Die Thickness	5.5 MILS
Gate Bonding Pad Area	7.1 x 7.1 MILS
Source Bonding Pad Area	60.4 x 35.6 MILS
Top Side Metalization	Al-Cu - 40,000Å
Back Side Metalization	Ti/Ni/Ag - 1,000Å/3,000Å/10,000Å
Scribe Alley Width	2.36 MILS
Wafer Diameter	8 INCHES
Gross Die Per Wafer	17,312

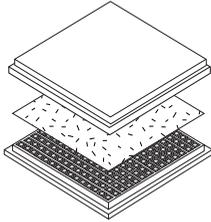
MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL		UNITS
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	20	V
Continuous Drain Current	I_D	9.93	A
Maximum Pulsed Drain Current	I_{DM}	37.44	A
Power Dissipation	P_D	1.92	W
Power Dissipation ($T_A=75^\circ\text{C}$)	P_D	1.15	W
Operating and Storage Junction Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
Thermal Resistance	Θ_{JA}	65	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{GSSF}, I_{GSSR}	$V_{GS}=20\text{V}, V_{DS}=0$			100	nA
I_{DSS}	$V_{DS}=30\text{V}, V_{GS}=0$			1.0	μA
BV_{DSS}	$V_{GS}=0, I_D=250\mu\text{A}$	30			V
$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu\text{A}$	1.0	1.48	3.0	V
V_{SD}	$V_{GS}=0, I_S=1.0\text{A}$			1.5	V
$r_{DS(ON)}$	$V_{GS}=10\text{V}, I_D=1.0\text{A}$		5.66	13	$\text{m}\Omega$
$r_{DS(ON)}$	$V_{GS}=4.5\text{V}, I_D=1.0\text{A}$		9.29	18	$\text{m}\Omega$

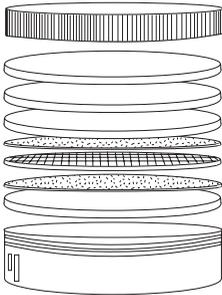
BARE DIE PACKING OPTIONS



BARE DIE IN TRAY (WAFFLE) PACK

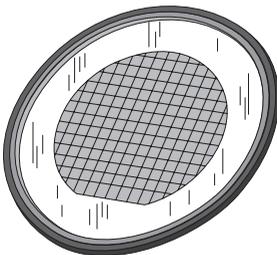
CT: Singulated die in tray (waffle) pack.
(example: CP211-PART NUMBER-CT)

CM: Singulated die in tray (waffle) pack 100% visually inspected as per MIL-STD-750, (method 2072 transistors, method 2073 diodes).
(example: CP211-PART NUMBER-CM)



UNSAWN WAFER

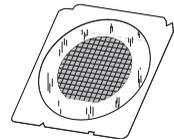
WN: Full wafer, unsawn, 100% tested with reject die inked.
(example: CP211-PART NUMBER-WN)



SAWN WAFER ON PLASTIC RING

WR: Full wafer, sawn and mounted on plastic ring,
100% tested with reject die inked.
(example: CP211-PART NUMBER-WR)

Please note: Sawn Wafer on Metal Frame (WS) is possible as a special order. Please contact your Central Sales Representative at 631-435-1110.



Visit the Central website for a complete listing of specifications:
www.centrasemi.com/bdspecs

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

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